

This cross-sectional diagram illustrates a semiconductor device. A central core, indicated by diagonal hatching, contains internal features labeled 120, 121, 122, 123, 124, and 125. The core is flanked by two main regions, 106 on the left and 108 on the right. Region 106 includes a layer 110 and a contact area 119. Region 108 includes a layer 111 and a contact area 119. Below the core, there are several horizontal layers or structures labeled 201, 217, 218, and 219. A dashed line indicates a symmetry plane through the center of the device.

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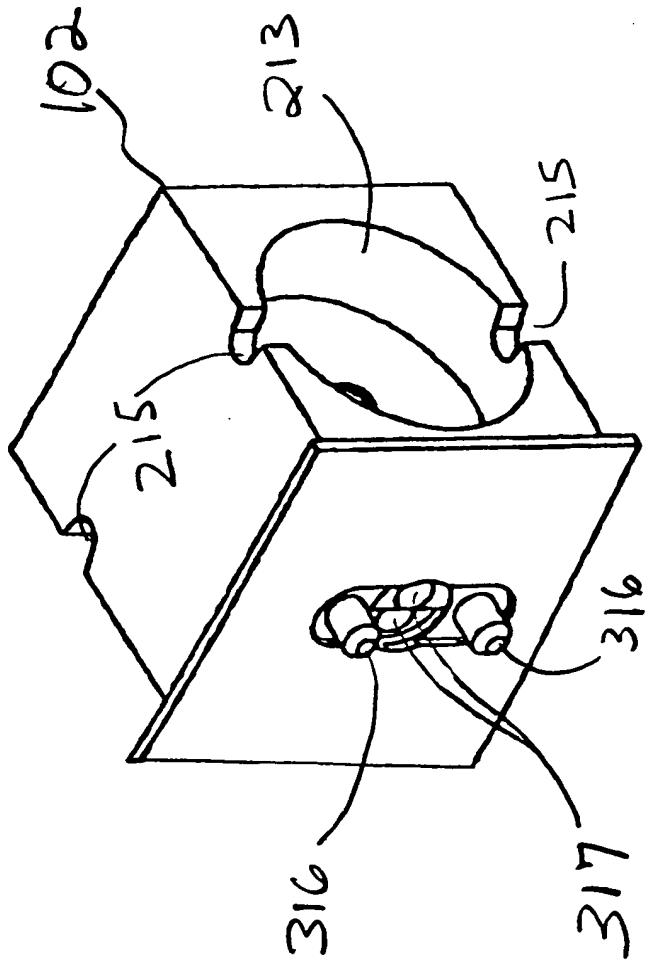


FIG. 3B

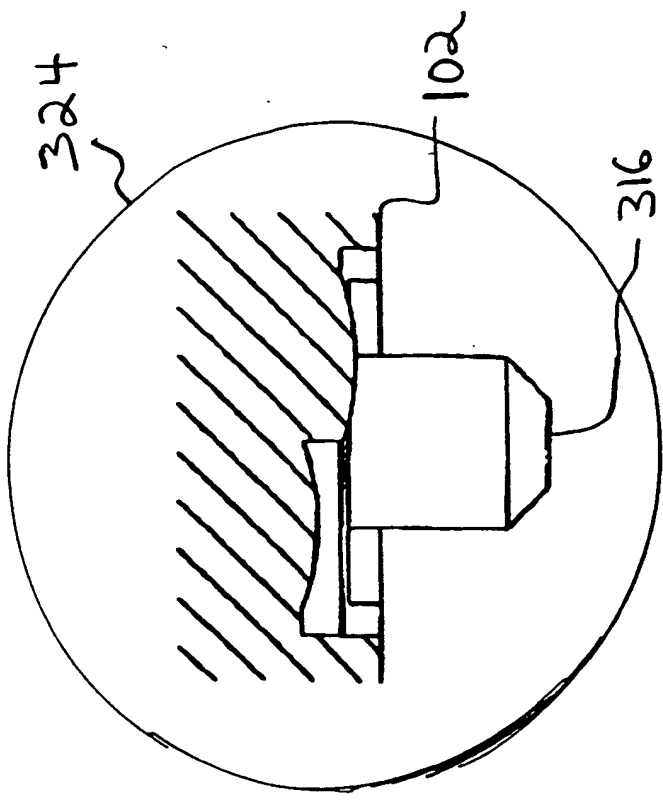
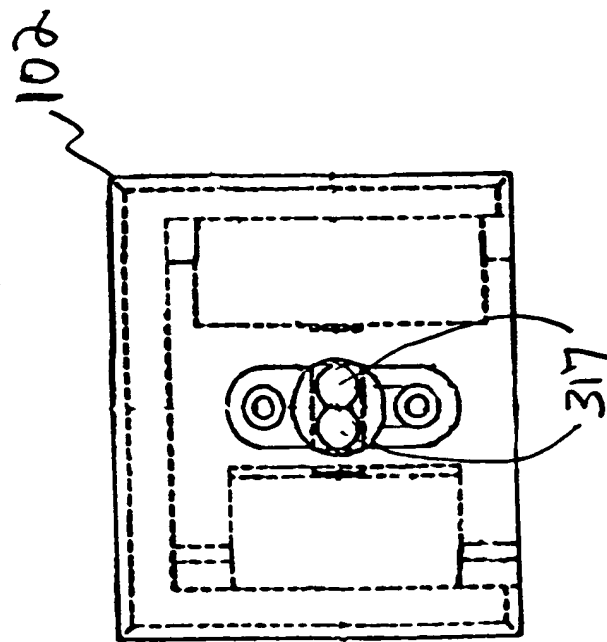


FIG. 3E

[illegible]

U
M
G
H
H

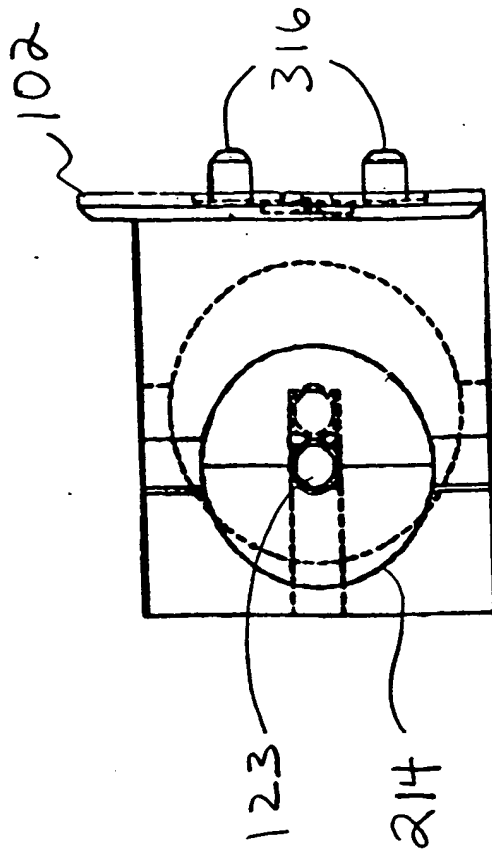


Fig. 34

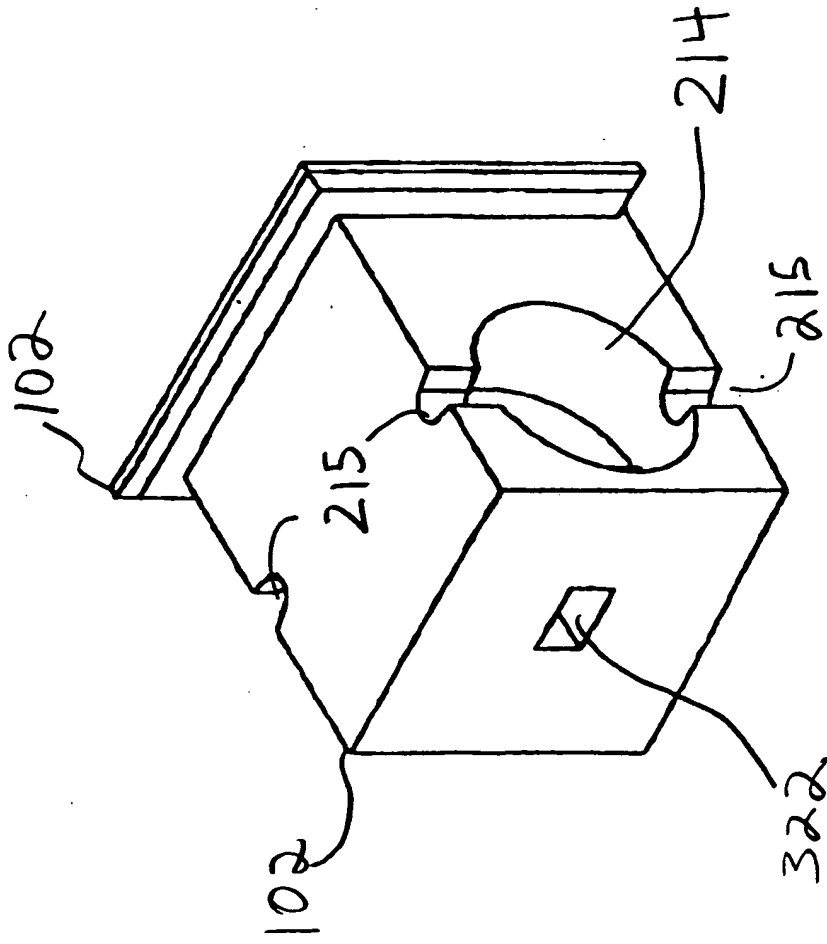


FIG. 3D

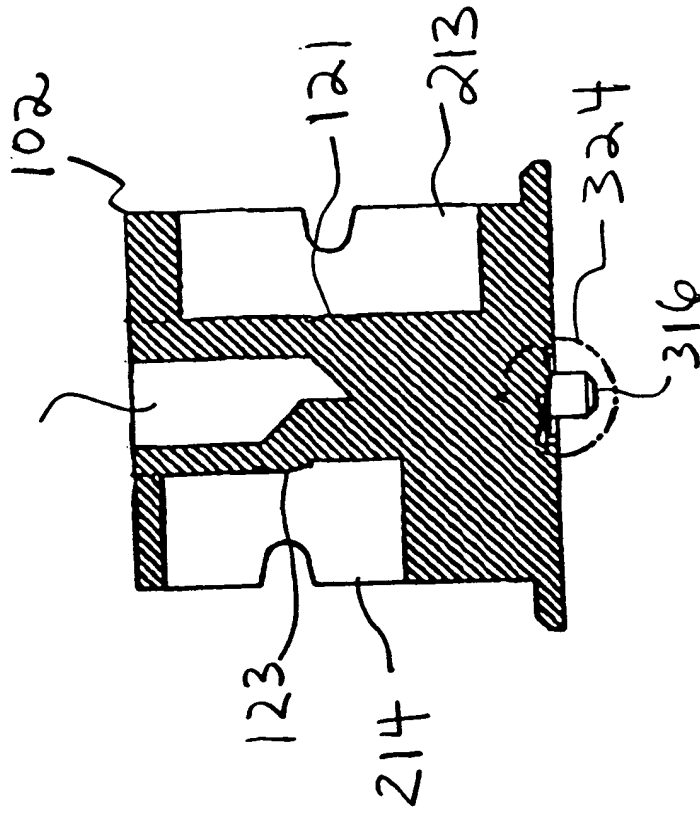


FIG. 3H

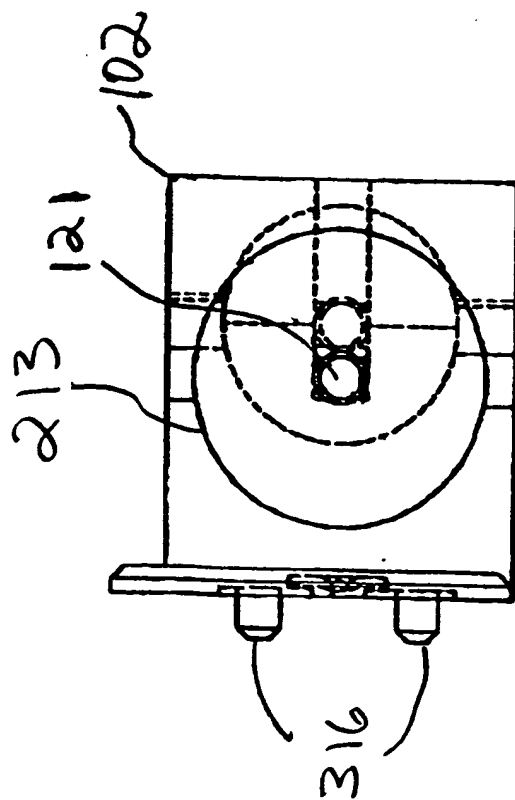


FIG. 36

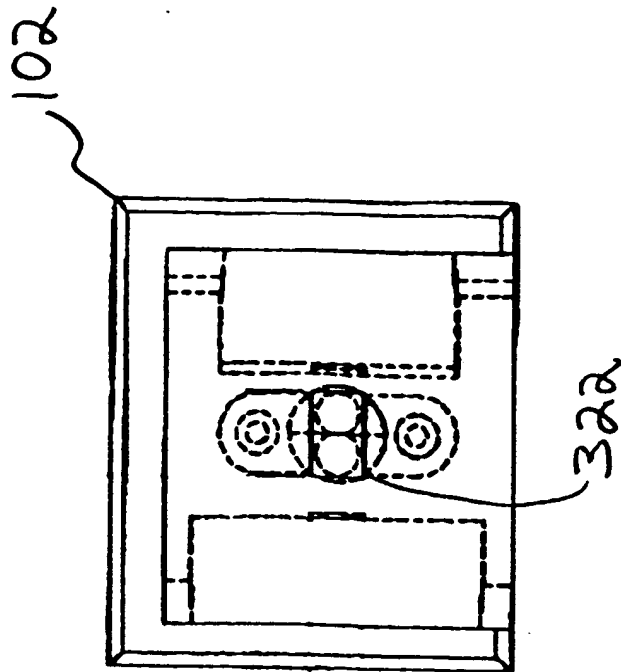


FIG. 3E

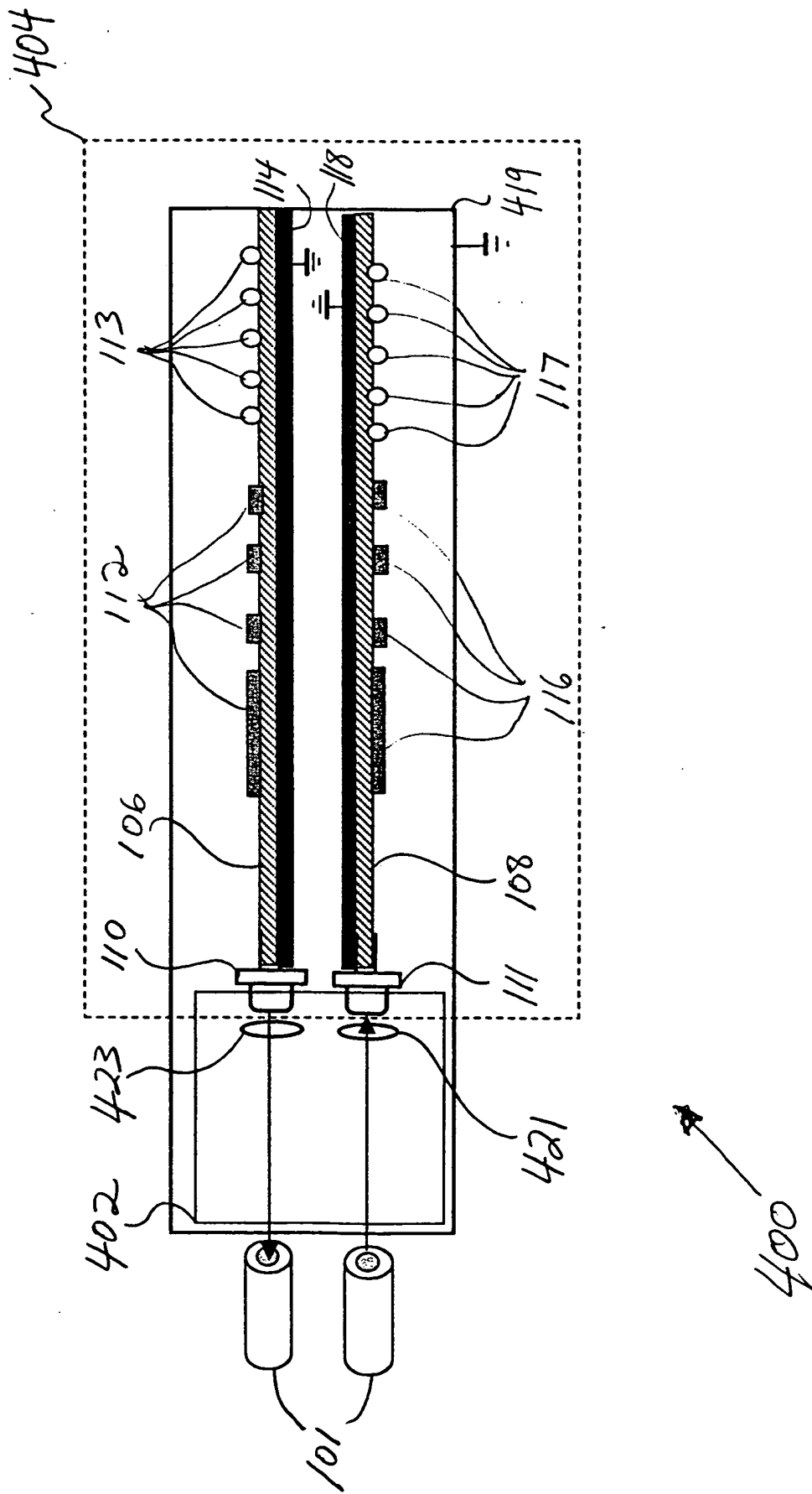


FIG. 4

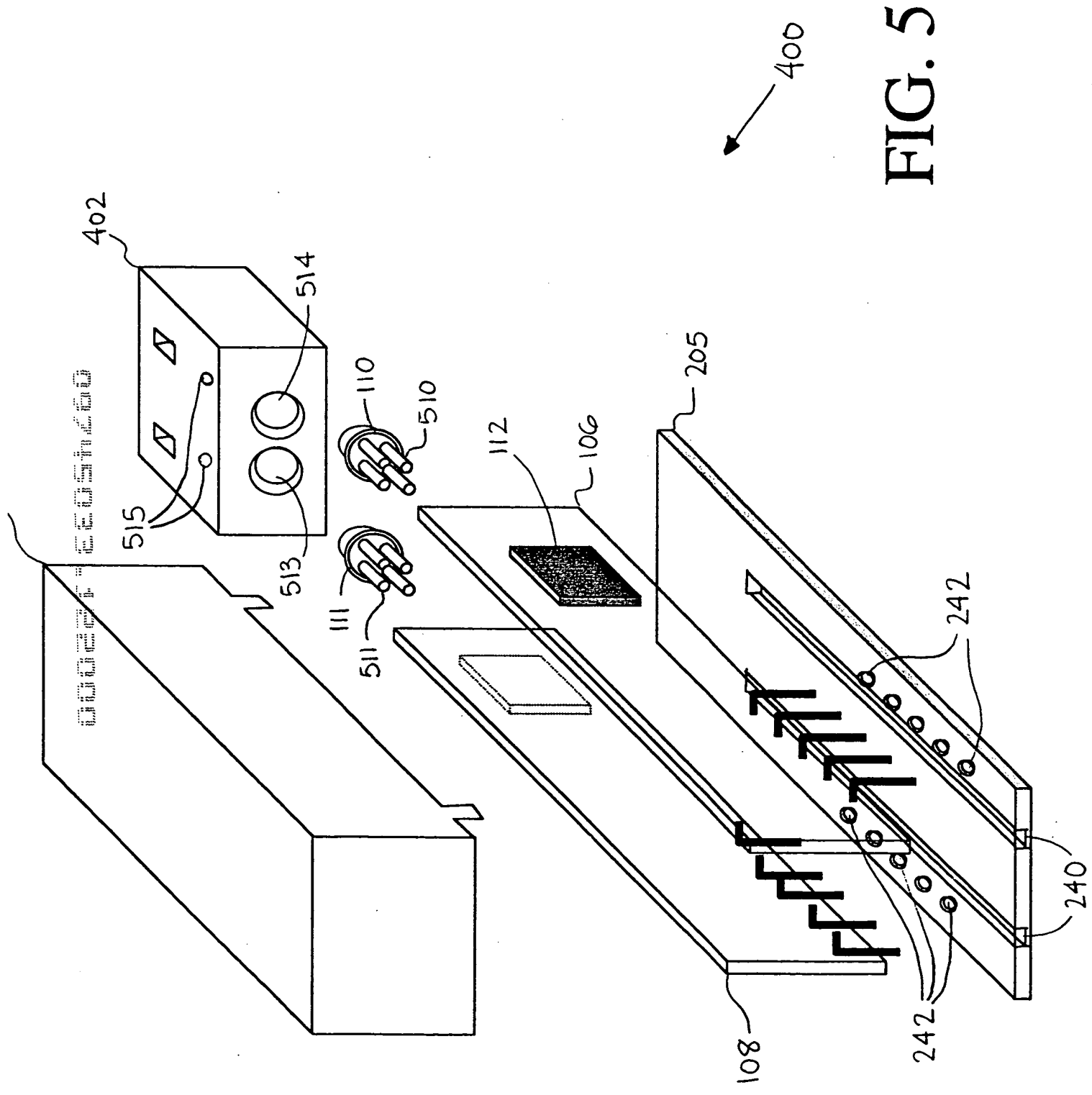
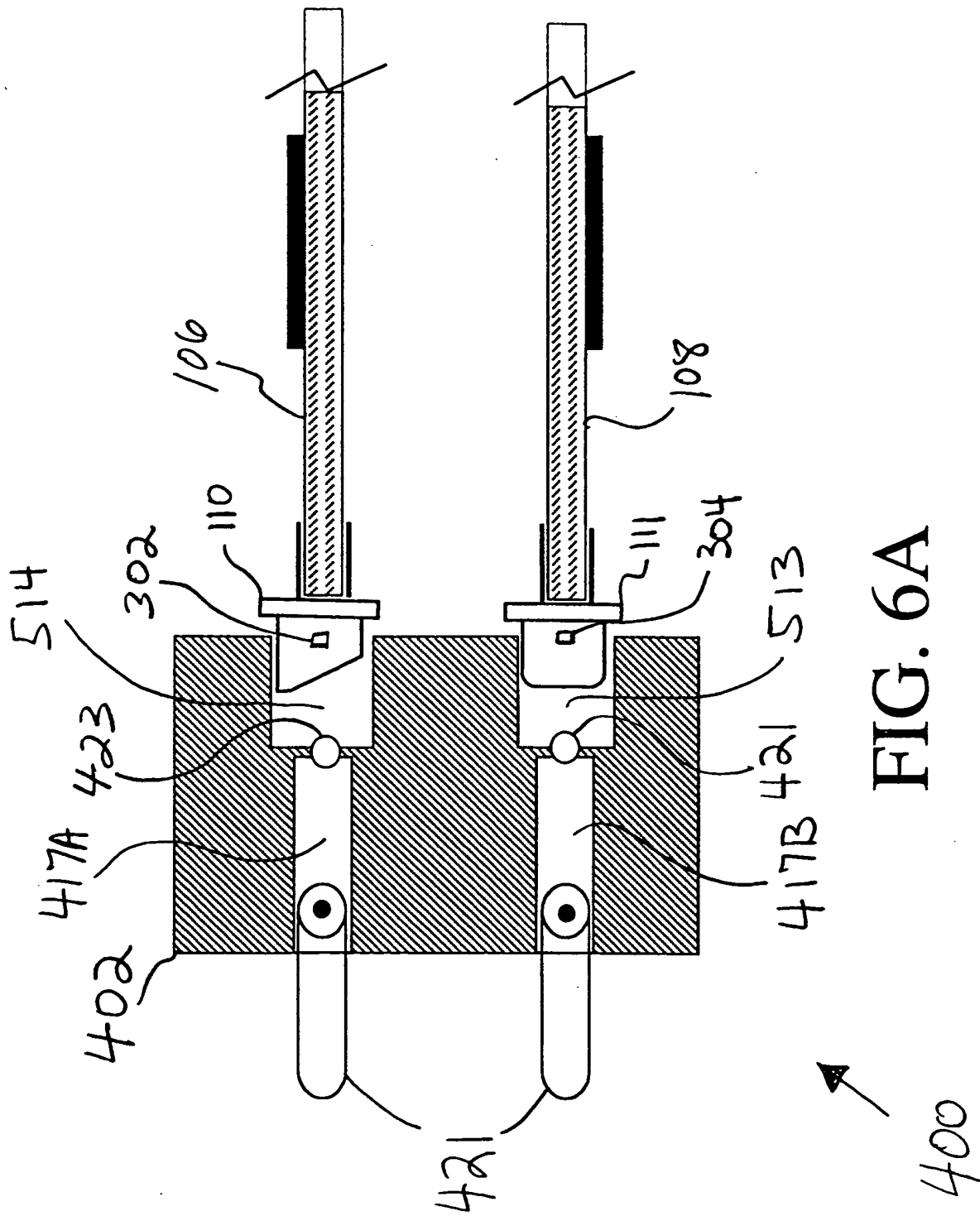


FIG. 5



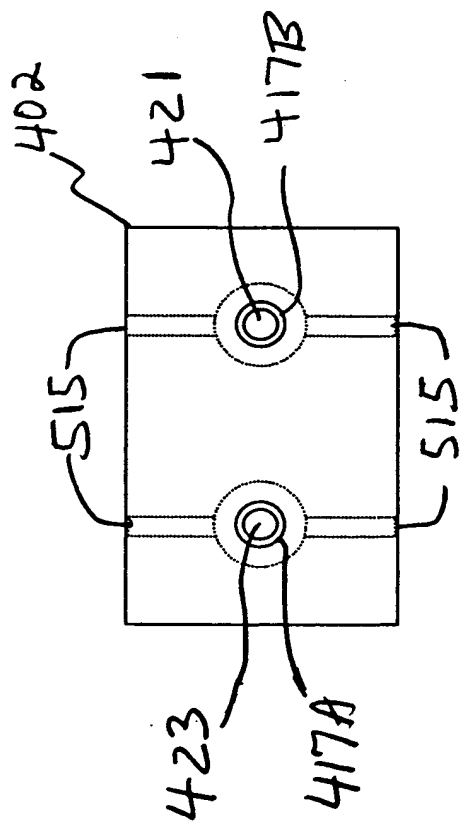


FIG. 6B

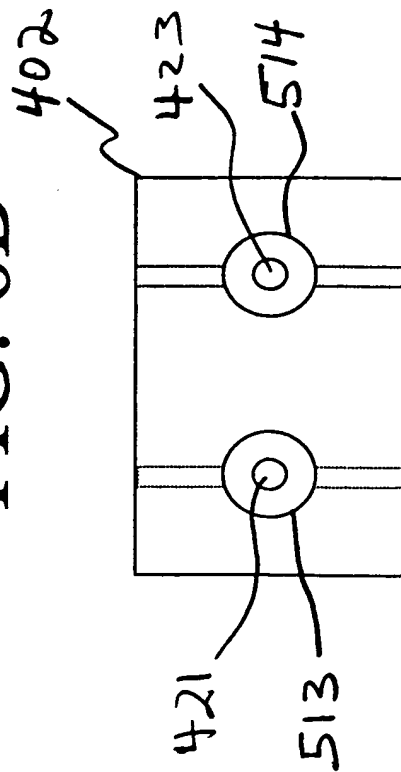


FIG. 6C

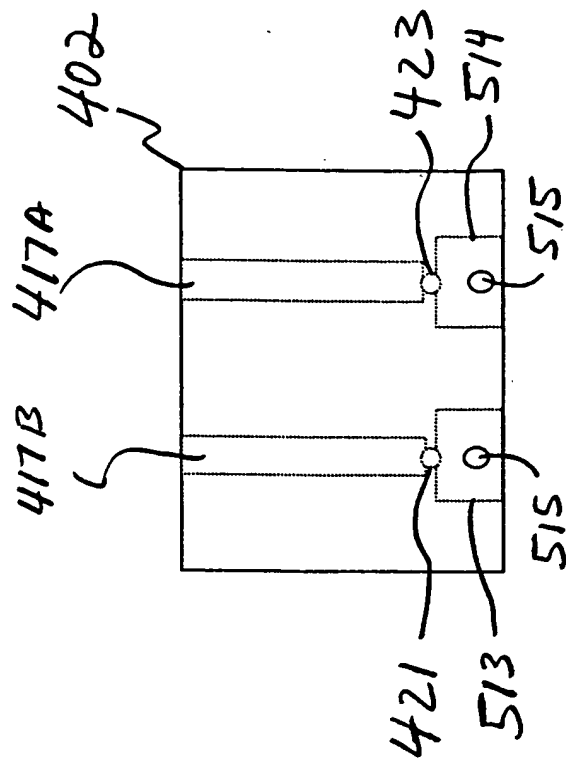


FIG. 6D

